



## Description

The AOB2606L can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-263, which accords with the RoHS standard.

## General Features

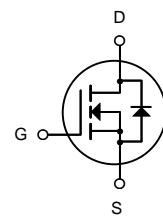
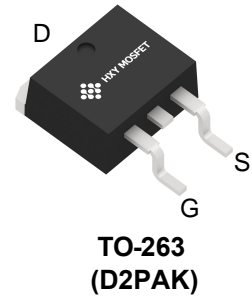
$V_{DS} = 60V$   $I_D = 90A$

$R_{DS(ON)} < 7.5m\Omega @ V_{GS}=10V$

## Application

Switching application

Power Management for Inverter Systems.



N-Channel MOSFET

## Ordering Information

Product ID	Pack	Brand	Units/Tube)
AOB2606L	TO-263(D2PAK)	HXY MOSFET	50

## Absolute Maximum Ratings ( $T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-Continuous	90	A
$I_D(100^\circ C)$	Drain Current-Continuous( $T_c=100^\circ C$ )	51	A
$I_{DM}$	Pulsed Drain Current	320	A
$P_D$	Maximum Power Dissipation	83	W
$E_{AS}$	Repetitive Avalanche Energy	244	mJ
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.5	$^\circ C/W$



**Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

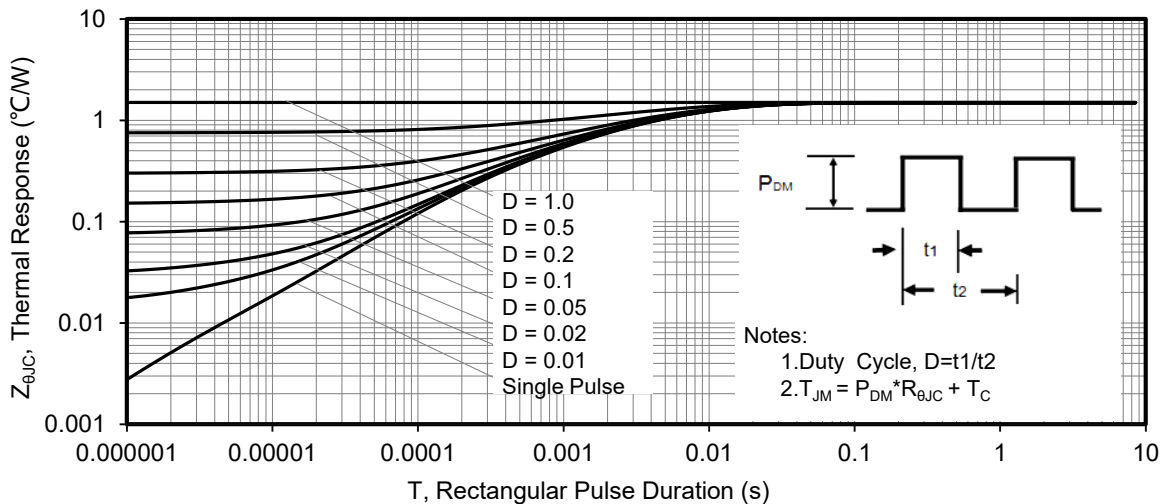
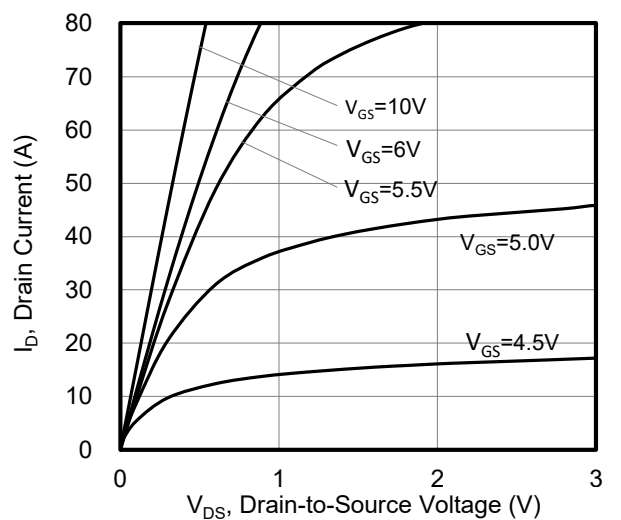
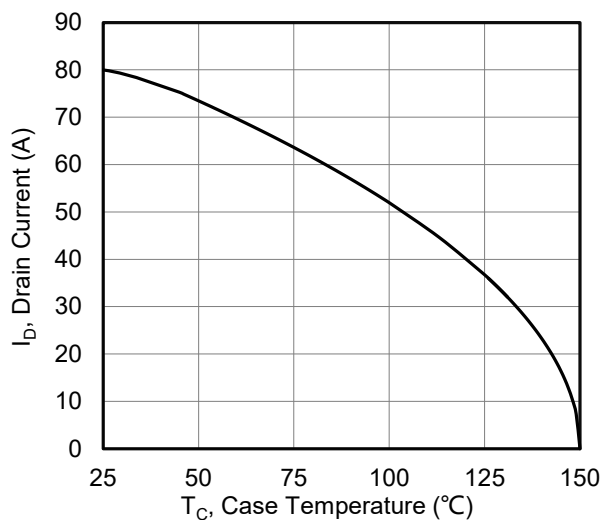
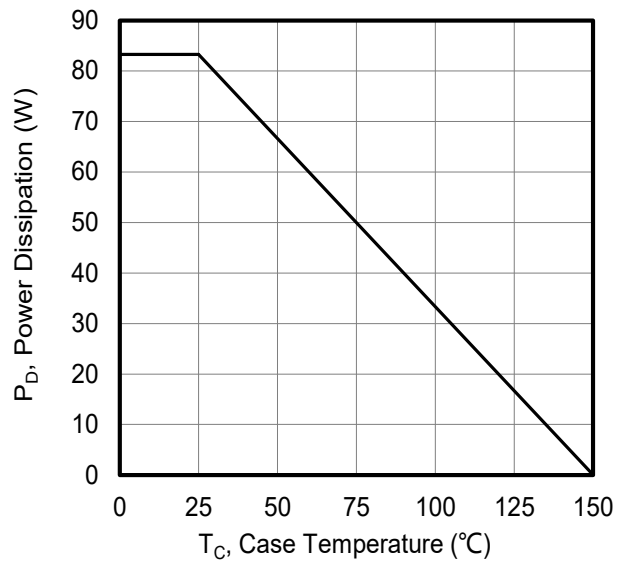
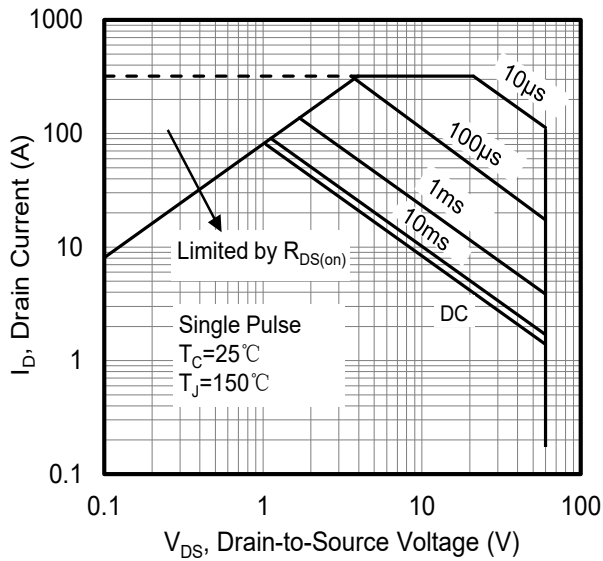
Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b><math>BV_{DSS}</math></b>	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	---	---	V
<b><math>I_{DSS}</math></b>	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=60V$	---	---	1	$\mu A$
<b><math>I_{GSS}</math></b>	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	$\pm 100$	nA
<b><math>V_{GS(th)}</math></b>	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	2	2.8	4	V
<b><math>R_{DS(on)}</math></b>	Drain-Source On Resistance	$V_{GS}=10V, I_D=20A$	---	5.8	7.5	m $\Omega$
<b><math>C_{iss}</math></b>	Input Capacitance	$V_{DS}=30V, V_{GS}=0V, f=1MHz$	---	4008	---	pF
<b><math>C_{oss}</math></b>	Output Capacitance		---	242	--	
<b><math>C_{rss}</math></b>	Reverse Transfer Capacitance		---	200	---	
<b><math>t_{d(on)}</math></b>	Turn-On Delay Time	$V_{DS}=30V, I_D=20A,$ $R_{ENG}=3\Omega, V_{GS}=10V$	---	18	---	ns
<b><math>t_r</math></b>	Rise Time		---	41	---	ns
<b><math>t_{d(off)}</math></b>	Turn-Off Delay Time		---	47	---	ns
<b><math>t_f</math></b>	Fall Time		---	28	---	ns
<b><math>Q_g</math></b>	Total Gate Charge	$V_{GS}=10V, V_{DS}=30V,$ $I_D=20A$	---	75	---	nc
<b><math>Q_{gs}</math></b>	Gate-Source Charge		---	18	---	nc
<b><math>Q_{gd}</math></b>	Gate-Drain "Miller" Charge		---	4.2	---	nc
<b><math>V_{SD}</math></b>	Diode Forward Voltage	$V_{GS}=0V, I_{SD}=20A$	---	---	1.2	V
<b><math>I_S</math></b>	Continuous Drain Current	$V_D=V_G=0V$	---	---	90	A
<b><math>I_{SM}</math></b>	Pulsed Drain Current		---	---	320	A
<b><math>T_{rr}</math></b>	Reverse Recovery Time	$I_F=20A, T_J=25^\circ C$	---	28	---	ns
<b><math>Q_{rr}</math></b>	Reverse Recovery Charge	$di/dt=100A/us$	---	52	---	nc

**Notes:**

1.  $L=0.5mH, V_{DD}=30V, \text{Start } T_J=25^\circ C.$
2. Limited by maximum junction temperature.
3. Repetitive Rating: Pulse width limited by maximum junction temperature.



### Typical Characteristics



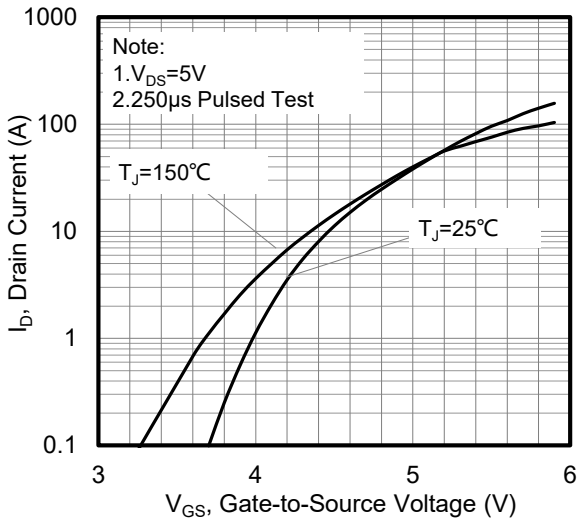


Figure 6. Typical Transfer Characteristics

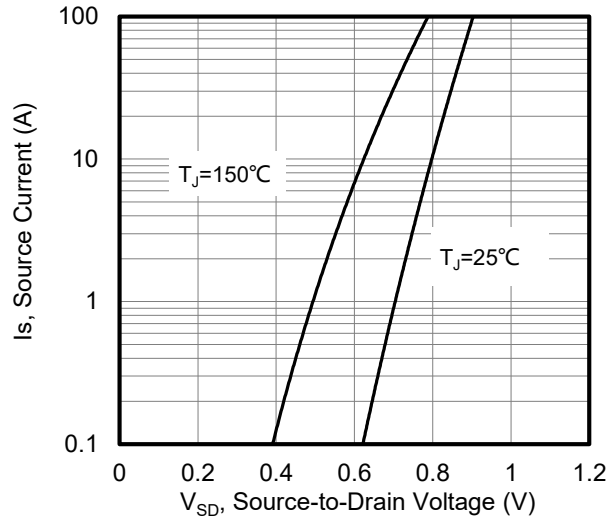


Figure 7. Typical Body Diode Transfer Characteristics

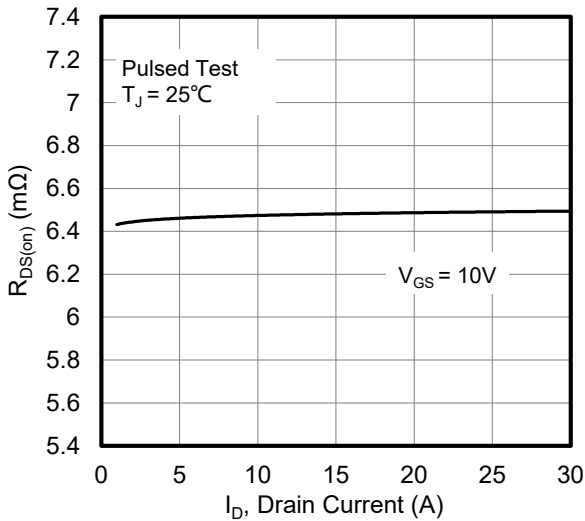


Figure 8. Drain-to-Source On Resistance vs Drain Current

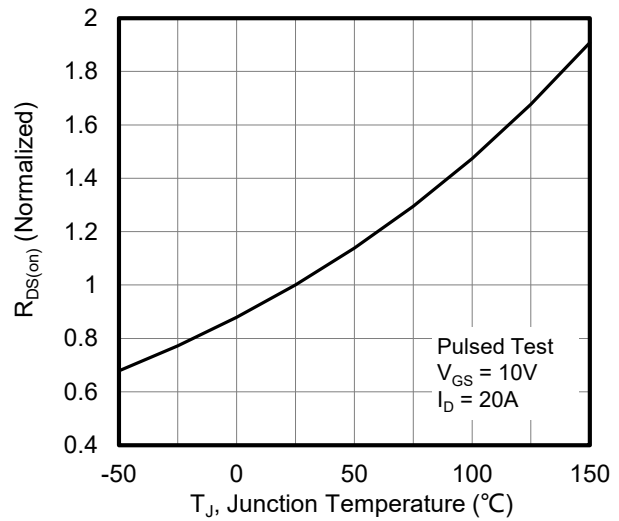


Figure 9. Normalized On Resistance vs Junction Temperature

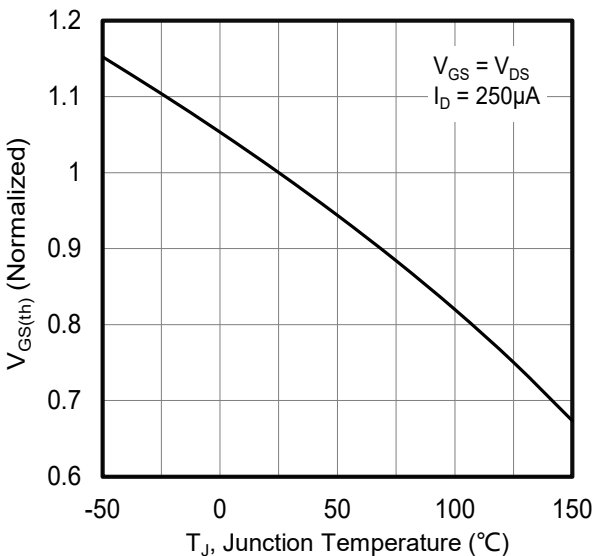


Figure 10. Normalized Threshold Voltage vs Junction Temperature

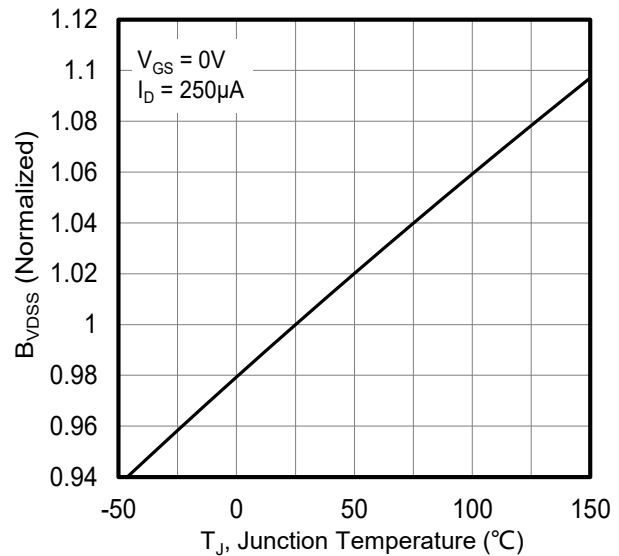


Figure 11. Normalized Breakdown Voltage vs Junction Temperature

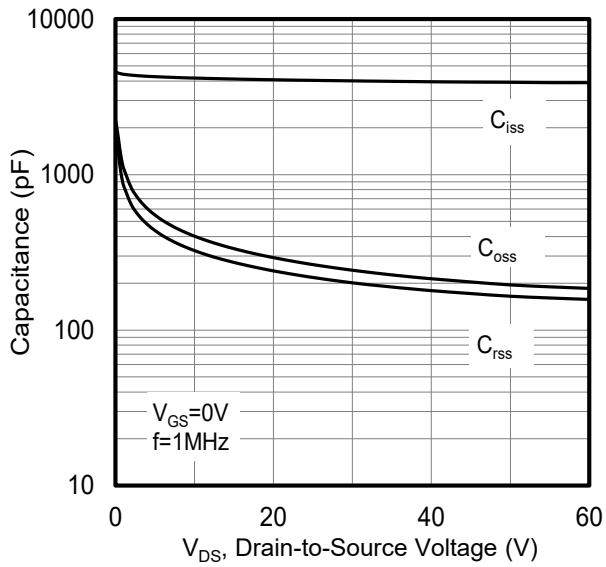


Figure 12. Capacitance Characteristics

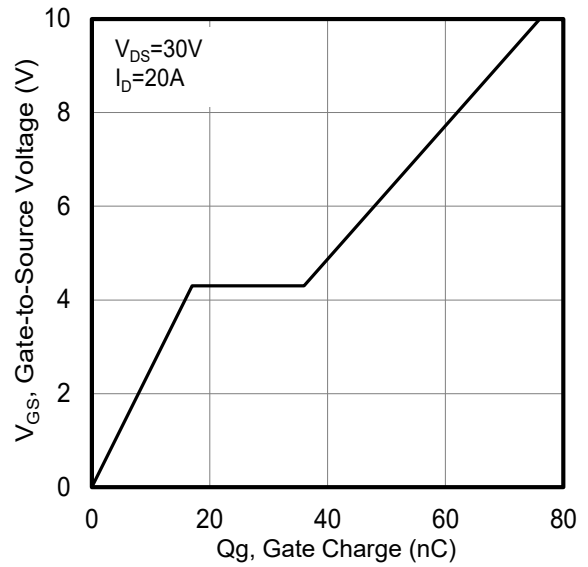
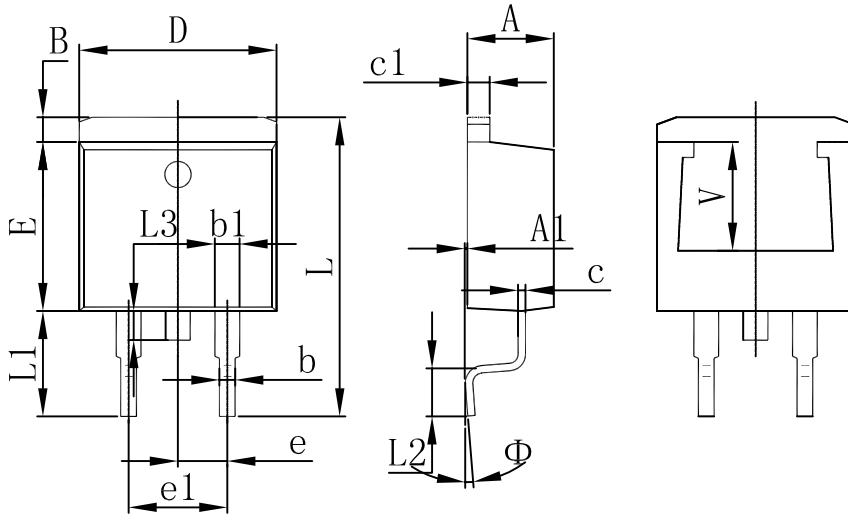


Figure 13. Typical Gate Charge vs Gate to Source Voltage



**TO-263(D2PAK)Package Outline Dimensions**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.120	1.420	0.044	0.056
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	14.940	15.500	0.588	0.610
L1	4.950	5.450	0.195	0.215
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
Φ	0°	8°	0°	8°
V	5.600 REF.		0.220REF.	



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